

ZXMN2A01F

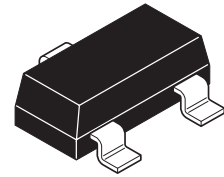
20V N-CANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 20V$; $R_{DS(ON)} = 0.12\Omega$; $I_D = 2.2A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



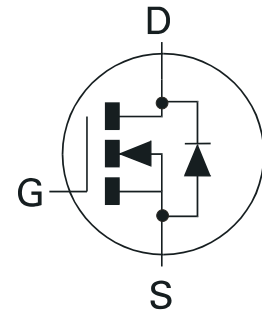
SOT23

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control



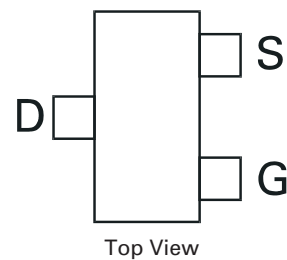
ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN2A01FTA	7"	8mm	3000 units
ZXMN2A01FTC	13"	8mm	10000 units

DEVICE MARKING

- 7N2

PINOUT



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current $V_{GS}=10V; T_A=25^\circ C$ (b) $V_{GS}=10V; T_A=70^\circ C$ (b) $V_{GS}=10V; T_A=25^\circ C$ (a)	I_D	2.2 1.7 1.9	A
Pulsed Drain Current (c)	I_{DM}	8	A
Continuous Source Current (Body Diode) (b)	I_S	1.29	A
Pulsed Source Current (Body Diode) (c)	I_{SM}	8	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	625 5	mW mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	806 6.4	mW mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

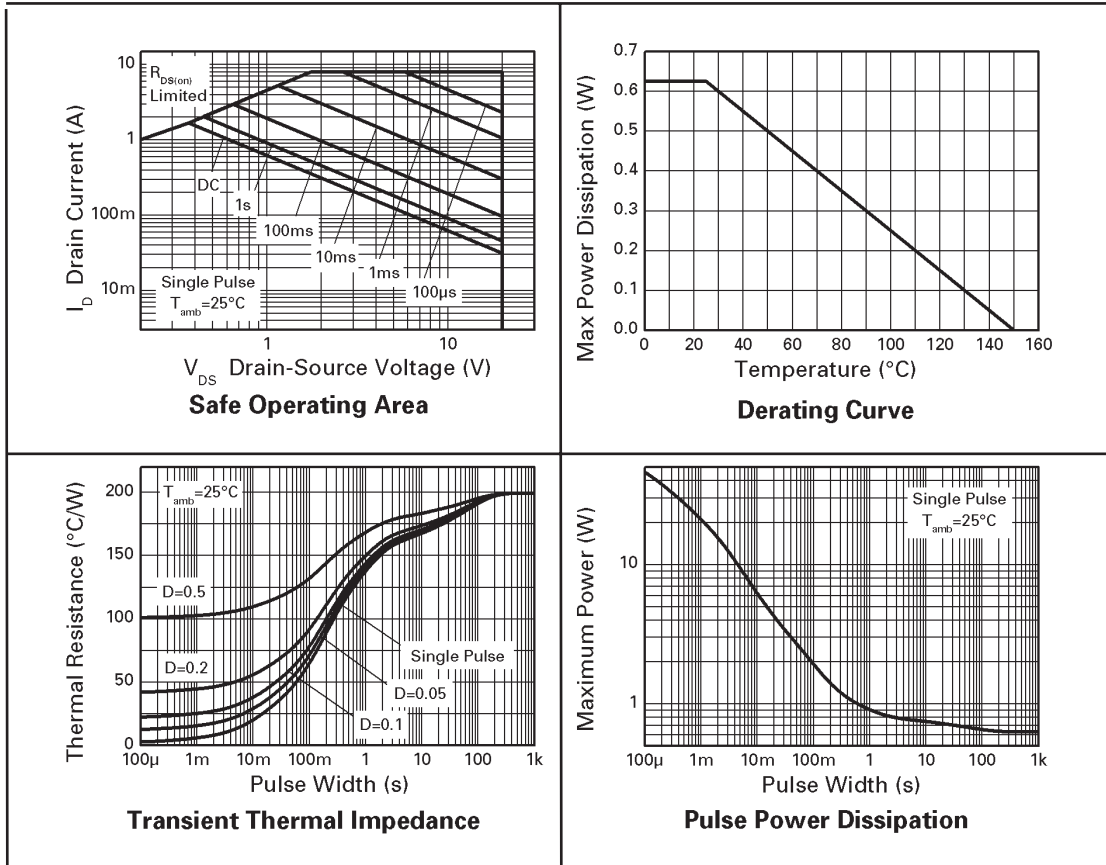
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	155	$^\circ C/W$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.
(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated)

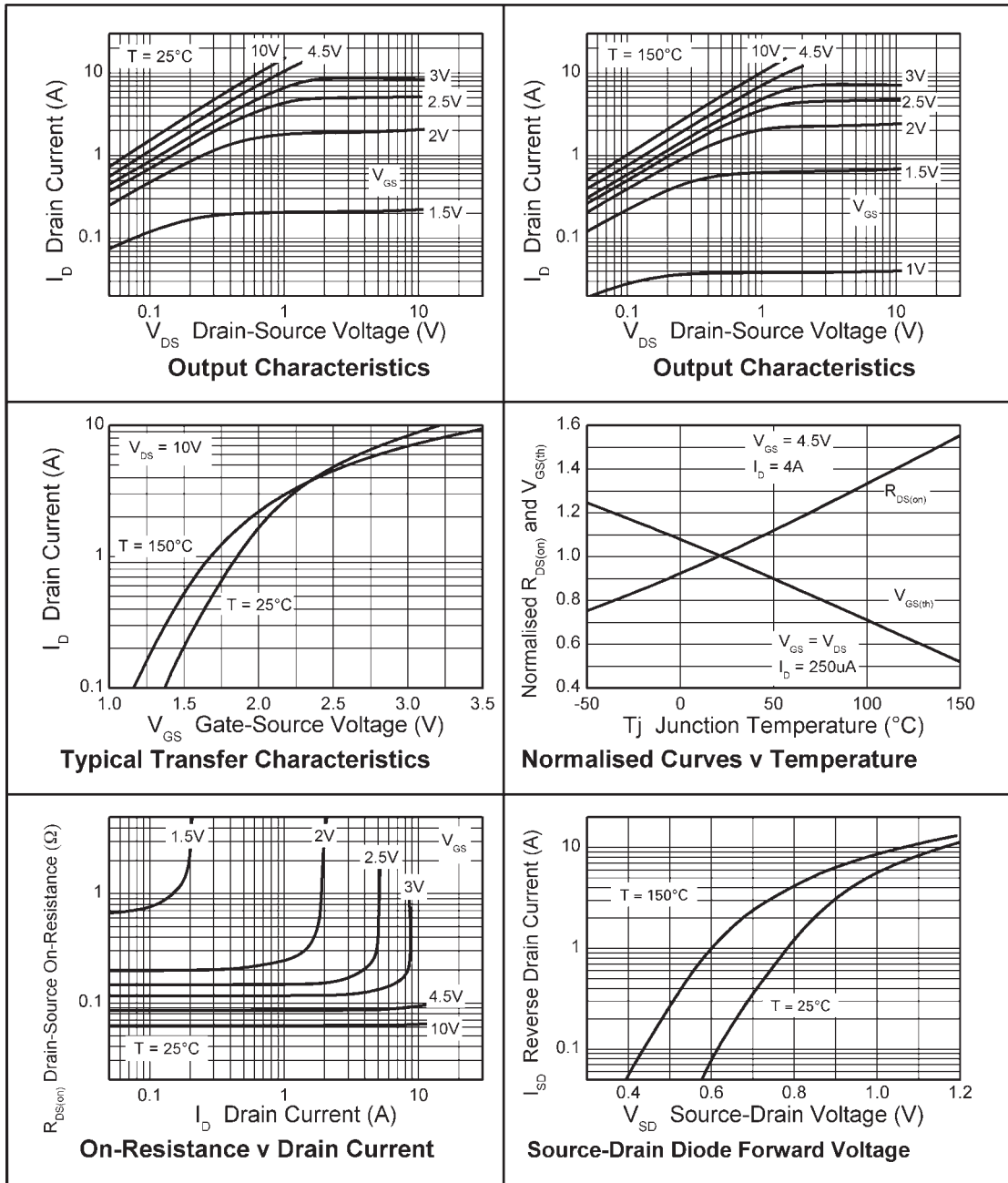
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	20			V	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			1	μA	$V_{DS}=20\text{V}$, $V_{GS}=0\text{V}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 12\text{V}$, $V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.7			V	$I_D=250\mu\text{A}$, $V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.12 0.225	Ω Ω	$V_{GS}=4.5\text{V}$, $I_D=4\text{A}$ $V_{GS}=2.5\text{V}$, $I_D=1.5\text{A}$
Forward Transconductance (1)(3)	g_{fs}		6.1		S	$V_{DS}=10\text{V}$, $I_D=4\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		303		pF	$V_{DS}=15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$
Output Capacitance	C_{oss}		59		pF	
Reverse Transfer Capacitance	C_{rss}		30		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		2.49		ns	$V_{DD}=10\text{V}$, $I_D=4\text{A}$ $R_G=6.0\Omega$, $V_{GS}=5\text{V}$
Rise Time	t_r		5.21		ns	
Turn-Off Delay Time	$t_{d(off)}$		7.47		ns	
Fall Time	t_f		4.62		ns	
Total Gate Charge	Q_g		3.0		nC	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=4\text{A}$
Gate-Source Charge	Q_{gs}		0.8		nC	
Gate-Drain Charge	Q_{gd}		1.0		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}		0.85	0.95	V	$T_J=25^\circ\text{C}$, $I_S=3.2\text{A}$, $V_{GS}=0\text{V}$
Reverse Recovery Time (3)	t_{rr}		23		ns	$T_J=25^\circ\text{C}$, $I_F=4\text{A}$, $di/dt=100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	Q_{rr}		5.65		nC	

NOTES:

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

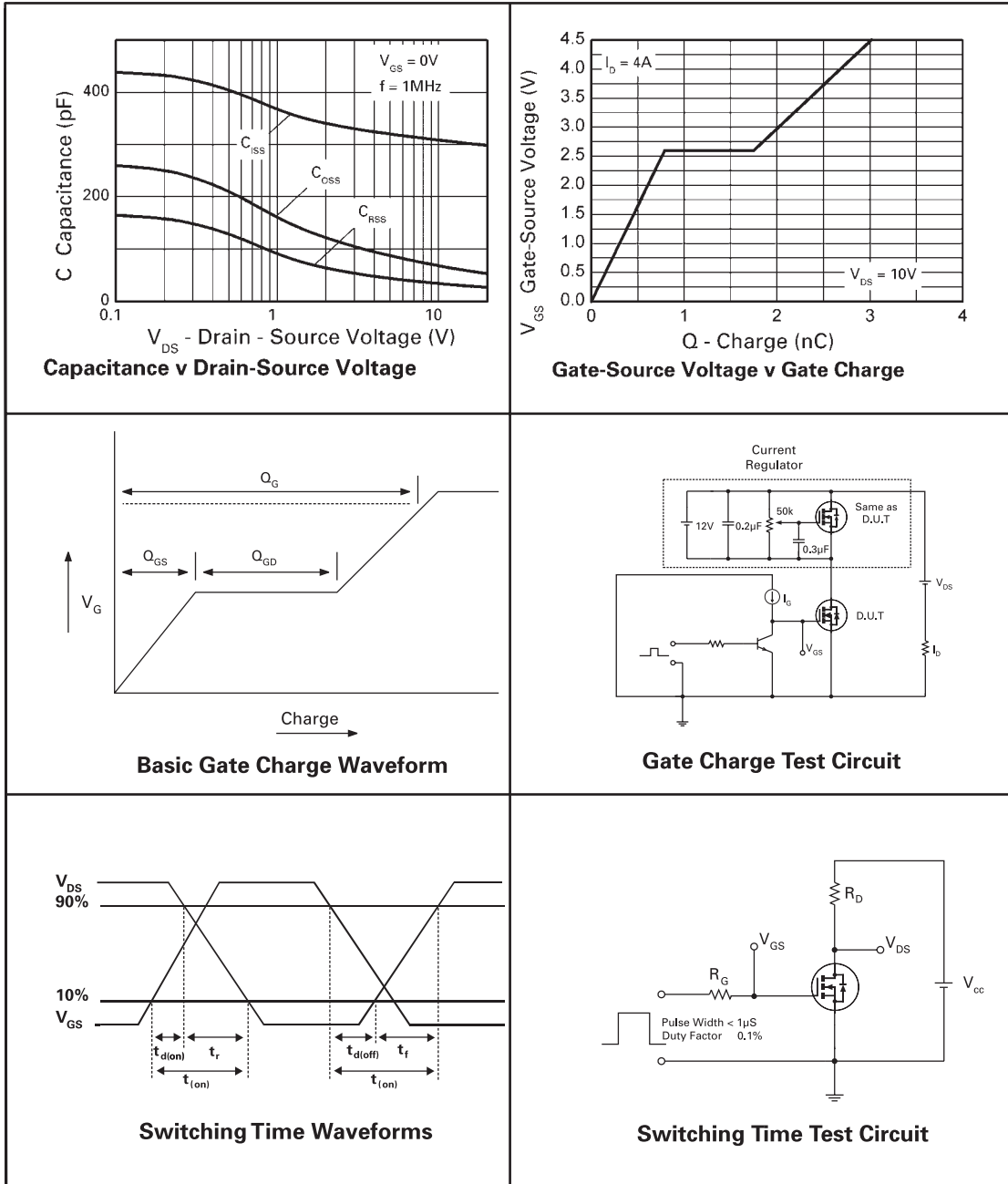
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TYPICAL CHARACTERISTICS



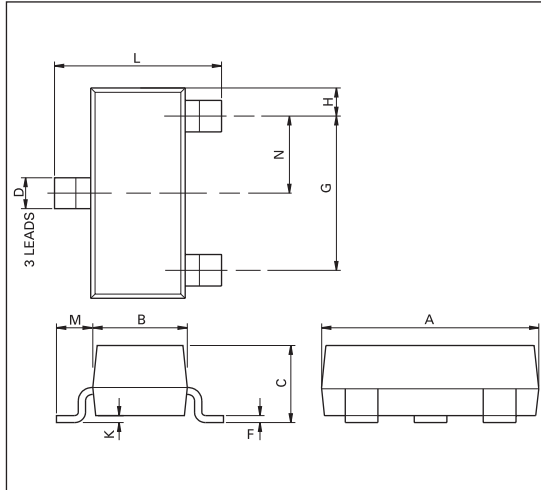
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TYPICAL CHARACTERISTICS

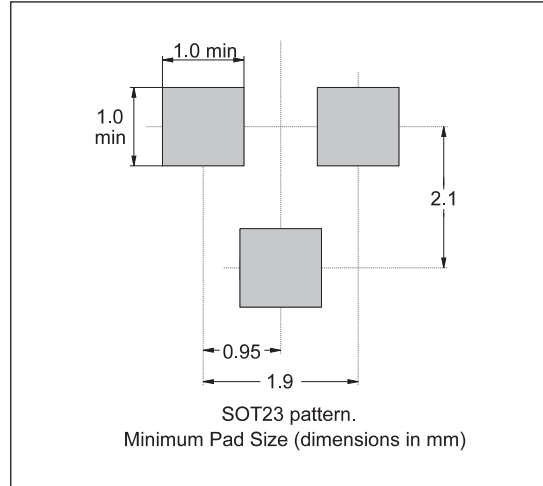


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PACKAGE OUTLINE



PAD LAYOUT



CONTROLLING DIMENSIONS IN MILLIMETERS APPROX CONVERSIONS INCHES

PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Max	Max
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	—	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		—	—		—	

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